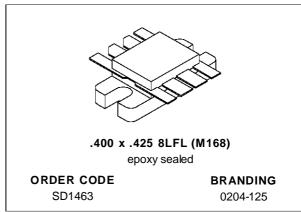


SD1463 (TCC0204-125)

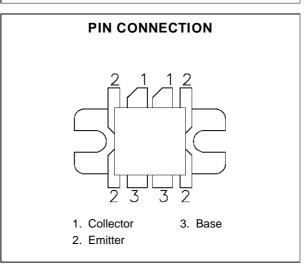
RF & MICROWAVE TRANSISTORS VHF/UHF APPLICATIONS

- 400 MHz
- 28 VOLTS
- EFFICIENCY 60%
- COMMON EMITTER
- GOLD METALLIZATION
- P_{OUT} = 125 W MIN. WITH 7.0 dB GAIN



DESCRIPTION

The SD1463 is a 28 V Class C gold metallized epitaxial silicon NPN planar transistor designed for UHF military and commercial equipment. The SD1463 is an internally matched, broadband device optimized for operation within the 225 - 400 MHz frequency range. This device utilizies diffused emitter resistors to achieve 10:1 VSWR load mismatch capability at rated operating conditions.



ABSOLUTE MAXIMUM RATINGS $(T_{case} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	15	А
P _{DISS}	Power Dissipation	270	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	- 65 to +150	°C

THERMAL DATA

R _{TH(j-c)} Junction-Case Thermal Resistance	0.65	°C/W
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August 23, 1996

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

Symbol		Test Conditions		Value		
Symbol	rest conditions		Min.	Typ.	Max.	Unit
ВУсво	I _C = 100 mA	$I_E = 0 \text{ mA}$	60	_		V
BVces	I _C = 80 mA	$V_{BE} = 0 V$	60	_	_	V
BV _{CEO}	I _C = 50 mA	$I_B = 0 \text{ mA}$	30	_		V
BV _{EBO}	I _E = 20 mA	$I_C = 0 \text{ mA}$	4.0	_		V
I _{CBO}	V _{CB} = 30 V	$I_E = 0 \text{ mA}$		_	10	mA
h _{FE}	V _{CE} = 5 V	I _C = 1 A	20	_	200	_

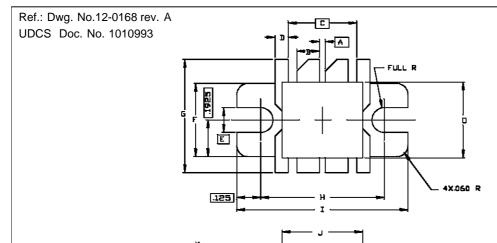
DYNAMIC

Symbol		Test Conditions		Value			Unit
Symbol		rest conditions		Min.	Тур.	Max.	Oiiit
PiN	f = 400 MHz	P _{OUT} = 125 W	$V_{CC} = 28 \text{ V}$	_		25	W
G _P	f = 400 MHz	P _{OUT} = 125 W	V _{CC} = 28 V	7.0			dB
ης	f = 400 MHz	P _{OUT} = 125 W	V _{CC} = 28 V	60	_	_	%

IMPEDANCE DATA

FREQ.	Z _{IN} (Ω)	Z _{CL} (Ω)		
225 MHz	0.5 + j 2.5	8.8 + j 3.5		
400 MHz	1.5 + j 1.7	5.0 + j 0.0		

PACKAGE MECHANICAL DATA



	SGS-THOMSON MIC	RUELECTRUNICS	1	CI	מידאכ
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
4	.03	1/0,76	к	.003/0,08	.007/0,18
В	.115/2,92	.125/3,18	L	.120/3,05	130/3,30
c	.36	0/9,14	м	.159/4,04	.175/4,45
ם	.065/1,65	.075/1,91	N		.280/7,11
E	13	0/3,30	מ	.395/10,03	.405/10,29
F	.380/9,65	.390/9,91			
G	.735/18,67	.765/19,43			
н	.645/16,38	.655/16,64			
1	.895/22,73	.905/22,99			
J	.420/10,67	.430/10,92]		

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